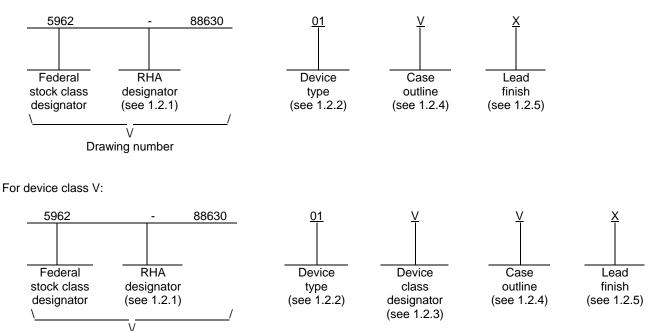
								ONS										
LTR	DESCRIPTION									DA	ATE (Y	R-MO-I	DA)		APPROVED			
А	Changes to s	slew rate te	st. Cha	nges IA	W NOF	R 5962-	R194-9	93.				93-0	08-25			M. A. FRYE		
В	Changes boi Add delta tes			-part nu	mbers.	Add d	levice ty	ype 03.				97-0)6-03		R. MONNIN			
С	Change to g	roup A subo	roups fo	or TCV	DOS in	table I.	Upda	te boile	rplate.	- rrp		00-1	0-26			R. MC	ONNIN	
D	Add device t	ype 01 limit	s to tabl	e I _{IB}	ro							02-1	1-22		R. MONNIN			
E	Drawing upd	lated to refle	ect curre	ent requ	iremen	ts ro)					06-0)5-16			R. MC	ONNIN	
F	Make chang and Table II	es to the V ₍ B ro	to the V _{OOS} test for device type 03 as specified					ied und	er Tabl	e I		08-0)7-01			R. HI	EBER	
THE ORIGINA	AL FIRST PAGE	OF THIS D	RAWIN	G HAS	BEEN I	REPLA	CED.											
REV	AL FIRST PAGE	OF THIS D	RAWIN	G HAS	BEENI	REPLA	CED.											
REV SHEET	AL FIRST PAGE	OF THIS D	RAWIN	G HAS	BEENI	REPLA	CED.											
REV SHEET REV	AL FIRST PAGE	OF THIS D	RAWIN	G HAS	BEENI	REPLA	CED.											
REV SHEET REV SHEET		OF THIS D		G HAS	BEEN I	REPLA	CED.	F	F	F	F	F	F	F	F	F		
REV SHEET REV SHEET REV STATUS	S S	RE		G HAS				F 4	F 5	F	F 7	F 8	F 9	F 10	F 11	F 12		
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	S	RE SH PR C	V EET EPARE	D BY	F 1	F	F		5	6 EFEN	7 SE SI	8 UPPL	9 .Y CE	10 NTEF	11	12 .UMB	US	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MIC R	S S	RE SF PR C CH W	V EET EPARE HARLES ECKED	D BY S E. BE BY J. JOHI	F 1 SORE	F	F		5	6 EFEN	7 SE SI DLUM	8 UPPL	9 .Y CE , OHI0	10 NTEF	11 R COL 218-3	12 .UMB	US	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICR DR THIS DRAW FOR	ANDARD S COCIRCUIT RAWING /ING IS AVAILAE USE BY ALL	RE SH PR C C CH W AP	V EET EPARE HARLES ECKED ILLIAM	D BY S E. BE BY J. JOHI	F 1 SORE	F	F	4 MIC	5 DE		7 SE SI DLUM http	8 IBUS ://ww	9 Y CE , OHIO /w.ds	10 NTEF O 432 CC.dl	11 R COL 218-3 a.mil	12 .UMB		
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A MICR MICR DR THIS DRAW FOR DEP, AND AGE	ANDARD ROCIRCUIT RAWING	RE RE PR C C CH W 3LE M DR	V EET EPARE HARLES ECKED ILLIAM PROVE CHAEL	D BY S E. BE BY J. JOHI D BY . A. FRY	F 1 SORE NSON	F 2	F	4 MIC	5 DE	6 EFEN CC	7 SE SI DLUM http	8 IBUS ://ww	9 Y CE , OHIO /w.ds	10 NTEF O 432 CC.dl	11 R COL 218-3 a.mil	12 -UMB 990		
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A MICR MICR DR THIS DRAW FOR DEP/ AND AGE DEPARTME	ANDARD S COCIRCUIT COCIRCUIT CAWING USE BY ALL PARTMENTS ENCIES OF THE	RE RE SH C C CH W AP SLE M SE DR	V EET EPARE HARLES ECKED ILLIAM PROVE CHAEL	D BY S E. BE BY J. JOHI D BY . A. FRY APPR(88-0 UEVEL	F 1 SORE NSON (E DVAL D D9-13	F 2	F	4 MIC AM	5 DE	6 EFEN CC CIRCU ER, I	7 SE SI DLUM http	8 UPPL BUS 0://ww LINE/ OLIT	9 Y CE , OHIO /w.ds	10 NTEF D 432 cc.dl	11 R COL 218-33 a.mil	12 -UMB 990	TION	

1. SCOPE

1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.

1.2 <u>PIN</u>. The PIN is as shown in the following examples.

For device classes M and Q:



Drawing number

1.2.1 <u>RHA designator</u>. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function			
01	AMP-01A	Low-noise, precision, instrumentation amplifier			
02	AMP-01B	Low-noise, precision, instrumentation amplifier			
03	AMP01	Low-noise, precision, instrumentation amplifier			

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as listed below. Since the device class designator has been added after the original issuance of this drawing, device classes M and Q designators will not be included in the PIN and will not be marked on the device.

Device class	<u>Device requirements documentation</u>								
М		Vendor self-certification to the requirements for MIL-STD-883 compliant, non- JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A							
Q or V	Certification and qualification to MIL-PRF-38535								
		1							
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1.2.4 <u>Case outline(s)</u>. The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
K	GDFP2-F24 or CDFP3-F24 GDIP1-T18 or CDIP2-T18	24 18	Flat pack Dual-in-line
v			
3	CQCC1-N28	28	Square leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/

Supply voltage (V _S)	±18 V dc
Power dissipation (P _D)	500 mW <u>2</u> /
Common mode input voltage	
Differential input voltage:	
$R_G \geq 2 \; k \Omega$	$\pm 20 \text{ V dc}$
R_{G} < 2 k Ω	±10 V dc
Output short circuit duration	
Storage temperature range	-65°C to +150°C
Lead temperature (soldering, 60 seconds)	
Thermal resistance, junction-to-case (θ_{JC})	See MIL-STD-1835
Thermal resistance, junction-to-ambient (θ_{JA}):	
Case V	120°C/W
Case 3	104°C/W
Case K	69°C/W

1.4 Recommended operating conditions.

Supply voltage (V _S)	$\pm 15 \text{ V dc}$
Ambient operating temperature range (T _A)	-55°C to +125°C

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883	-	Test Method Standard Microcircuits.
MIL-STD-1835	-	Interface Standard Electronic Component Case Outlines.

<u>1</u>/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

2/ Must withstand the added PD due to short circuit test, e.g., IOS.

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DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings. MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 <u>Case outlines</u>. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535.

3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 <u>Notification of change for device class M</u>. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.

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		Conditions <u>1</u> /	Group A	Device	Limits		
Test	Symbol	$\label{eq:tau} \begin{array}{l} -55^\circ C \leq T_A \leq +125^\circ C \\ \text{unless otherwise specified} \end{array}$	subgroups	type	Min	Max	- Unit
Input bias current			1	01, 03		±4	nA
	IB		2, 3			±10	
			1	02		±6	_
			2, 3			±15	
Input offset current			1	01, 03		1	nA
	I _{IO}		2, 3			3	_
			1	02		2 6	_
Offset referred to input vs. positive supply	+PSR	V+ = +5 V to +15 V, V- = -15 V, G = 1000	2, 3 1, 2, 3	01, 03	120	0	dB
		V = -15 V, G = 1000 V = +5 V to +15 V, V = -15 V, G = 100			110		
		V+ = +5 V to +15 V, V- = -15 V, G = 10			95		
		V+ = +5 V to +15 V, V- = -15 V, G = 1			75		
		V+ = +5 V to +15 V, V- = -15 V, G = 1000		02	110		
		V+ = +5 V to +15 V, V- = -15 V, G = 100			100		
		V+ = +5 V to +15 V, V- = -15 V, G = 10			90		
		V+ = +5 V to +15 V, V- = -15 V, G = 1			70		
Offset referred to input vs. negative supply	-PSR	V- = -5 V to -15 V, V+ = +15 V, G = 1000	1, 2, 3	All	105		dB
		V- = -5 V to -15 V, V+ = +15 V, G = 100			90		
		V- = -5 V to -15 V, V+ = +15 V, G = 10			70		
		V- = -5 V to -15 V, V+ = +15 V, G = 1			50		-
See footnote at end of table.							

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TABLE I. Electrical performance characteristics – Continued.												
Test	Symbol	Conditions <u>1</u>		Group		Device	Lim	its	Linit			
1631	Symbol	$-55^{\circ}C \le T_A \le +12$ unless otherwise sp		subgro	ups	type	Min	Max	- Unit			
Common mode rejection	CMR	$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 1000	1		01, 03	125		dB			
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 100				120					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 10				100					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 1				85					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 1000	2, 3	3		120					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 100				115					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 10			02	95					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 1				80		-			
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 1000	1			115					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 100				110					
			$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 10				95				
					$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 1				75		
						$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 1000	2, 3	2, 3		110	
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 100				105					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	= 10				90					
		$V_{CM} = \pm 10 \text{ V}, 1 \text{ k}\Omega$ source imbalance, G	6 = 1				75					
See footnote at end of table.									_			
			1					I				
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Test	Symbol	Conditions <u>1</u> /	Group A	Device	e Limits		Unit
Test	Symbol	$\label{eq:tau} \begin{array}{l} -55^\circ C \leq T_A \leq +125^\circ C \\ \text{unless otherwise specified} \end{array}$	subgroups	type	Min	Max	
Gain equation accuracy	GE	$G = 20R_S / R_G, T_A = +25^{\circ}C$	1	01		0.6	%
		Accuracy measured at $G = 1, 10, 100, and 1000$		02, 03		0.8]
Gain range	G	T _A = +25°C	1	All	1	1000	V/V
Output short circuit	I _{OS+}	T _A = +25°C	1	All	60	120	mA
current	I _{OS-}				-120	-60	
Reference input resistance	RINREF	T _A = +25°C	1	All	35	65	kΩ
Quiescent current	IQ	+V linked to +V _{OP} -V linked to -V _{OP}	1, 2, 3	All		4.8	mA
Input offset voltage	VIOS		4	01		50	μV
			5, 6	1		80	
			4	02, 03		100	
			5, 6			150	
Output offset voltage	Voos		4	01		3	mV
			5, 6			6	
			4	02		6	
			5, 6			10	
			4, 5, 6	03		10	
Output offset voltage		De u	8	01, 03		50	μV/°C
drift	ICV00S	TCV _{OOS} $R_G = \infty$		02		120	1

TARIFI	Electrical	nerformance	characteristics	
TADLE I.	LIEUIIUAI	penomiance	characteristics	- Continueu.

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TABLE I. Electrical performance characteristics – Continued.							
Test	Symbol	Conditions <u>1</u> / Group A		Limits Limits		nits	L locit
Test	Symbol	$-55^{\circ}C \le T_A \le +125^{\circ}C$ unless otherwise specified	subgroups	type	Min	Max	Unit
Output voltage swing	Vo	R _L = 500 Ω, 2 kΩ	4	All	±13		V
		R _L = 50 Ω			±2.5		
		R _L = 500 Ω, 2 kΩ	5, 6		±12		
Slew rate	SR	G = 10	4	01	3.5		V/µs
			5, 6		2.75		
			4	02, 03	3.0		
			5, 6		2.0		
Average input offset	TCVIOS	T _A = -55°C, +125°C	8	01	0.3		μV/°C
voltage drift	10105	TA = -55 0, +125 0	5	02, 03	1.0		μν, Ο

 $\underline{1}/~V_S$ = $\pm 15~V,~R_S$ = 10 k\Omega, R_L = 2 kΩ, unless otherwise specified.

3.9 Verification and review for device class M. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 49 (see MIL-PRF-38535, appendix A).

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Device types	01 and 02		03
Case outlines	V	3	К
Terminal number		Terminal symbol	
1	R _G	NC	R _{G2}
2	R _G	R _G	R _{G1}
3	-IN	R _G	-IN
4	V _{OOS} NULL	-IN	NC
5	V _{OOS} NULL	NC	VOOSNULL
6	TEST PIN	V _{OOS} NULL	NC
7	SENSE	NC	VOOSNULL
8	REFERENCE	VOOSNULL	TEST PIN
9	OUTPUT	NC	NC
10	-V _{OP}	TEST PIN	NC
11	V-	NC	SENSE
12	V+	SENSE	REFERENCE
13	+V _{OP}	REFERENCE	OUTPUT
14	Rs	OUT	-V _{OP}
15	Rs	NC	NC
16	VIOSNULL	-V _{OP}	V-
17	VIOSNULL	NC	V+
18	+IN	V-	+V _{OP}
19		V+	NC
20		NC	R _{S2}
21		+V _{OP}	R _{S1}
22		R _S	VIOSNULL
23		R _S	VIOSNULL
24		NC	+IN
25		V _{IOS} NULL	
26		VIOSNULL	
27		NC	
28		+IN	

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4. VERIFICATION

4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

- a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.

4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 7, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

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Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgr (in accord: MIL-PRF-385	ance with
	Device	Device	Device
	class M	class Q	class V
Interim electrical	1	1	1
parameters (see 4.2)			
Final electrical	1, 2, 3, 4, 5, <u>1</u> /	1, 2, 3, 4, <u>1</u> /	1, 2, 3, <u>1/ 2</u> /
parameters (see 4.2)	6, 8	5, 6, 8	4, 5, 6, 8
Group A test	1, 2, 3, 4, 5, 6, 8	1, 2, 3, 4, 5,	1, 2, 3, 4, 5,
requirements (see 4.4)		6, 8	6, 8
Group C end-point electrical	1	1	1 <u>2</u> /
parameters (see 4.4)			
Group D end-point electrical	1	1	1
parameters (see 4.4)			
Group E end-point electrical			
parameters (see 4.4)			

TABLE IIA. Electrical test requirements.

<u>1</u>/ PDA applies to subgroup 1.

2/ Delta limits in accordance with table IIB shall be computed with reference to the previous interim electrical parameters.

Parameter	Device type	Limit		Delta	
Falametei	Device type	Min	Max	Min	Max
VIOS	01		50 μV		40 μV
	03		100 μV		40 μV
Voos	01		3 mV		6 mV
	03		10 mV		10 mV
I _{B+}	01, 03		4 nA		3 nA
I _{B-}	01, 03		4 nA		3 nA

Table IIB. 240 hour burn-in and group C end-point electrical parameters.

4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
- b. $T_A = +125^{\circ}C$, minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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4.4.2.2 <u>Additional criteria for device classes Q and V</u>. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table IIA herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at

 $T_A = +25^{\circ}C \pm 5^{\circ}C$, after exposure, to the subgroups specified in table IIA herein.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractorprepared specification or drawing.

6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.

6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 08-07-01

Approved sources of supply for SMD 5962-88630 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DSCC maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

	1	1
Standard	Vendor	Vendor
microcircuit drawing	CAGE	similar
PIN 1/	number	PIN 2/
<u>FIN 1/</u>	number	F IIN <u>Z</u> /
5962-8863001VA	<u>3</u> /	AMP-01AX/883
5962-8863001VKA	<u>3</u> /	AMP01AN/QMLV
5962-8863001VVA	24355	AMP01AD/QMLV
5962-8863001V3A	24355	AMP01ATC/QMLV
5962-8863002VA	<u>3</u> /	AMP-01BX/883
5962-88630023A	<u>3</u> /	AMP-01BTC/883
5962-8863003VKA	24355	AMP01N/QMLV
5962-8863003VVA	24355	AMP01D/QMLV
5962-8863003V3A	24355	AMP01TC/QMLV

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- <u>2</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- <u>3/</u> Not available from an approved source of supply.

Vendor CAGE number Vendor name and address

24355

Analog Devices Route 1 Industrial Park P.O. Box 9106 Norwood, MA 02062 Point of contact: 7910 Triad Center Drive Greensboro, NC 27409-9605

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.